Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed for back-to-back SCR output devices for solid state relays or applications requiring high surge operation.

- Photo Glass Passivated Blocking Junctions for High Temperature Stability, Center Gate for Uniform Parameters
- 400 Amperes Surge Capability
- Blocking Voltage to 600 Volts
- Device Marking: Logo, Device Type, e.g., MCR264-4, Date Code

MAXIMUM RATINGS (T_{.J} = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to 125°C, Sine Wave 50 to 60 Hz; Gate Open)	VDRM, VRRM		Volts	
MCR264-4 MCR264-6 MCR264-8		200 400 600		
On-State RMS Current (T _C = 80°C; 180° Conduction Angles)	IT(RMS)	40	А	
Average On-State Current (T _C = 80°C; 180° Conduction Angles)	I _{T(AV)}	25	А	
Peak Non-repetitive Surge Current (T _C = 80°C) (1/2 Cycle, Sine Wave 60 Hz,	ITSM	400	A	
$T_J = 125$ °C)		450		
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)	PGM	20	Watts	
Forward Average Gate Power (t = 8.3 ms, T _C = 80°C)	PG(AV)	0.5	Watt	
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 80°C)	I _{GM}	2.0	А	
Operating Junction Temperature Range	TJ	-40 to +125	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

(1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

These devices are rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.

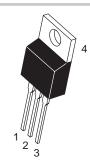


ON Semiconductor

http://onsemi.com

SCRs 40 AMPERES RMS 200 thru 600 VOLTS





TO-220AB CASE 221A STYLE 3

PIN ASSIGNMENT		
1	Cathode	
2	Anode	
3	Gate	
4	Anode	

ORDERING INFORMATION

Device	Package	Shipping
MCR264-4	TO220AB	500/Box
MCR264-6	TO220AB	500/Box
MCR264-8	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

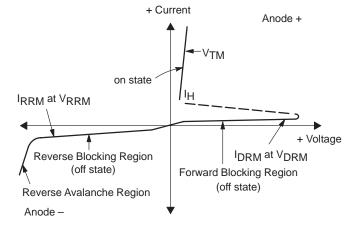
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•		•	
Peak Repetitive Forward or Reverse Blocking Current (V_{AK} = Rated V_{DRM} or V_{RRM} , Gate Open) $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _{DRM} , I _{RRM}	_	_	10 2.0	μA mA
ON CHARACTERISTICS					
Peak Forward On–State Voltage ⁽¹⁾ (I _{TM} = 80 A)	VTM	_	1.4	2.0	Volts
Gate Trigger Current (Continuous dc) $(V_{AK} = 12 \text{ Vdc}, R_L = 100 \text{ Ohms}, T_C = -40^{\circ}\text{C})$	^I GT	_	15 30	50 90	mA
Gate Trigger Voltage (Continuous dc) (V _{AK} = 12 Vdc, R _L = 100 Ohms)	V _{GT}	_	1.0	1.5	Volts
Gate Non-Trigger Voltage (V _{AK} = 12 Vdc, R _L = 100 Ohms, T _J = 125°C)	V _{GD}	0.2	_	_	Volts
Holding Current (V _{AK} = 12 Vdc, Initiating Current = 200 mA, Gate Open)	lн	_	30	60	mA
Turn-On Time $(I_{TM} = 40 \text{ A}, I_{GT} = 60 \text{ mAdc})$	t _{gt}	_	1.5	_	μs
DYNAMIC CHARACTERISTICS					
Critical Rate-of-Rise of Off-State Voltage (Gate Open, $V_D = Rated V_{DRM}$, Exponential Waveform)	dv/dt	_	50	_	V/µs

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
IRRM	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
I⊔	Holding Current



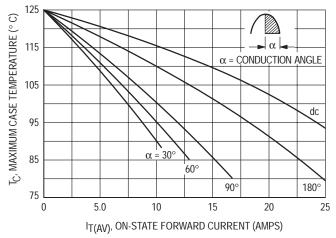


Figure 1. Average Current Derating

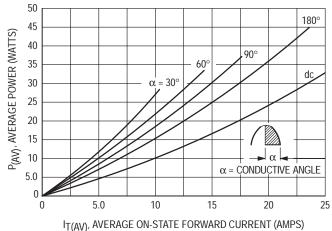
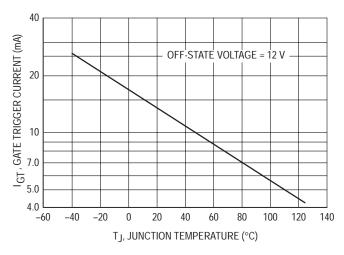


Figure 2. Maximum On-State Power Dissipation



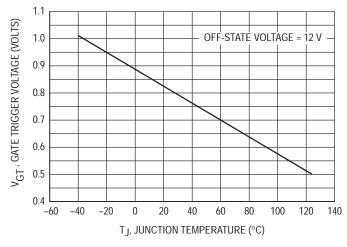
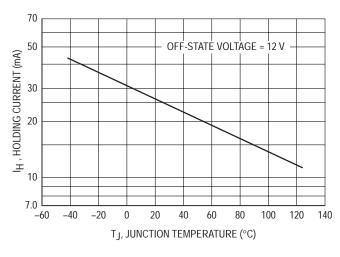


Figure 3. Typical Gate Trigger Current





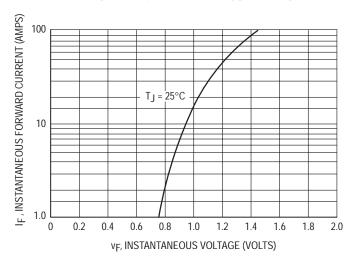


Figure 5. Typical Holding Current

Figure 6. Typical Forward Voltage

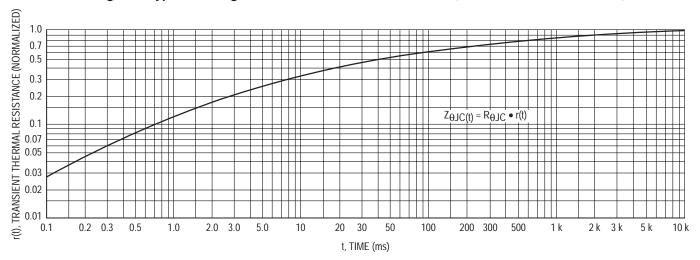
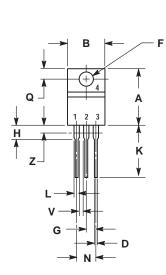
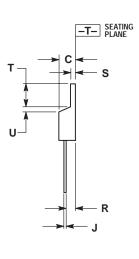


Figure 7. Thermal Response

PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE Z





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

- STYLE 3: PIN 1. CATHODE 2. ANODE

 - 3. GATE 4. ANODE

Notes

Notes

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